

Supporting Materials

Janus MoAZ_3H ($\text{A}=\text{Ge}, \text{Si}; \text{Z}=\text{N}, \text{P}, \text{As}$) monolayers: a new class of semiconductors exhibiting excellent photovoltaic and catalytic performances

Xiaolin Cai^{1*}, Guoxing Chen¹, Rui Li¹, Weiyang Yu¹, Xuefeng Yang¹, Yu Jia^{2,3*}

¹School of Physics and Electronic Information Engineering, Henan Polytechnic University, Jiaozuo 454000, China

²Key Laboratory for Special Functional Materials of Ministry of Education, Collaborative Innovation Center of Nano Functional Materials and Applications, School of Material Science and Engineering, Henan University, Kaifeng 475004, China

³International Laboratory for Quantum Functional Materials of Henan, and School of Physics and Microelectronics, Zhengzhou University, Zhengzhou 450001, China

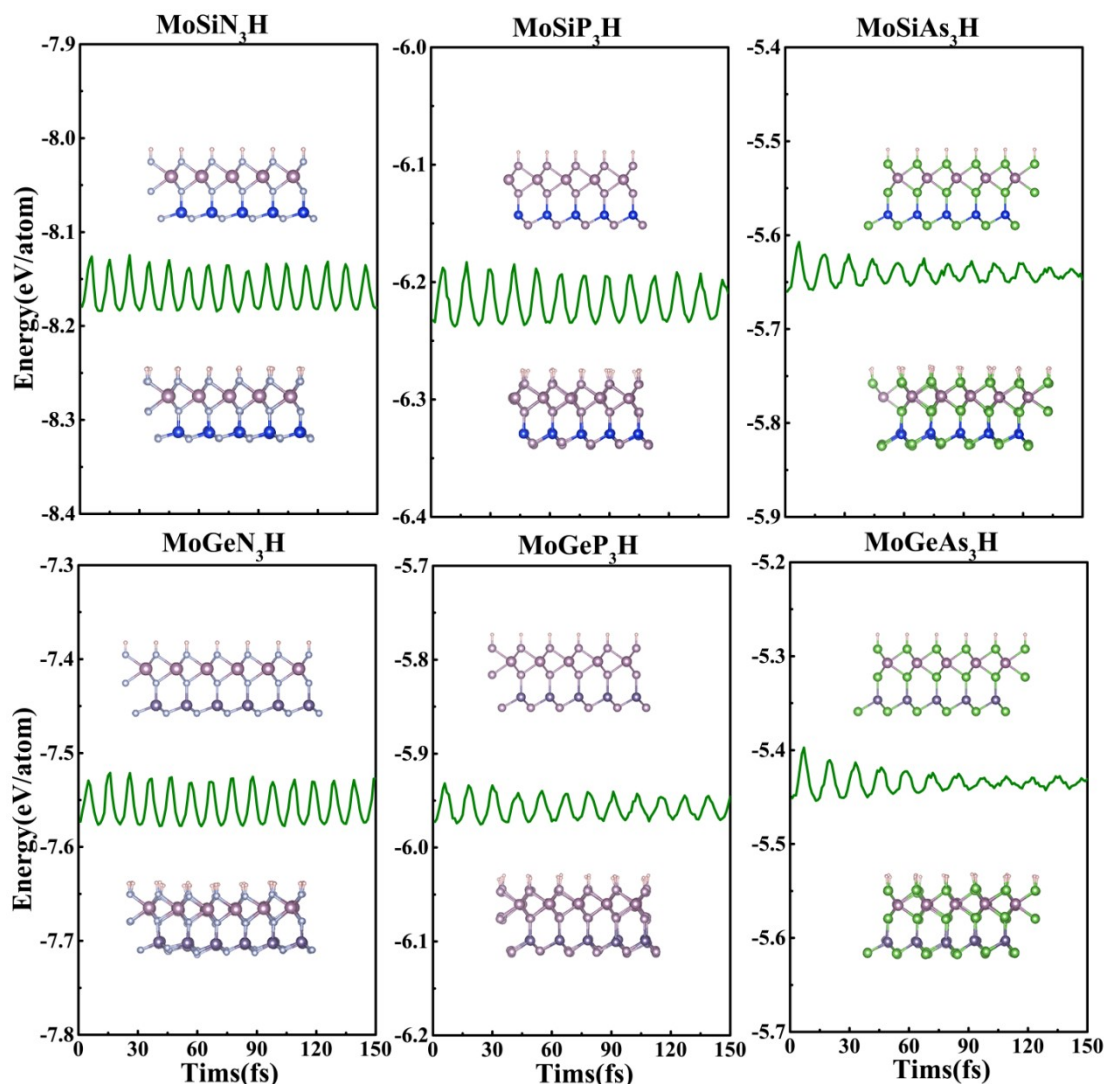


Fig. S1 AIMD simulation of MoAZ_3H ML material, in which the green curve is the evolution of the energy per atom over time, and the top and bottom insets are the initial and final structures,

respectively.

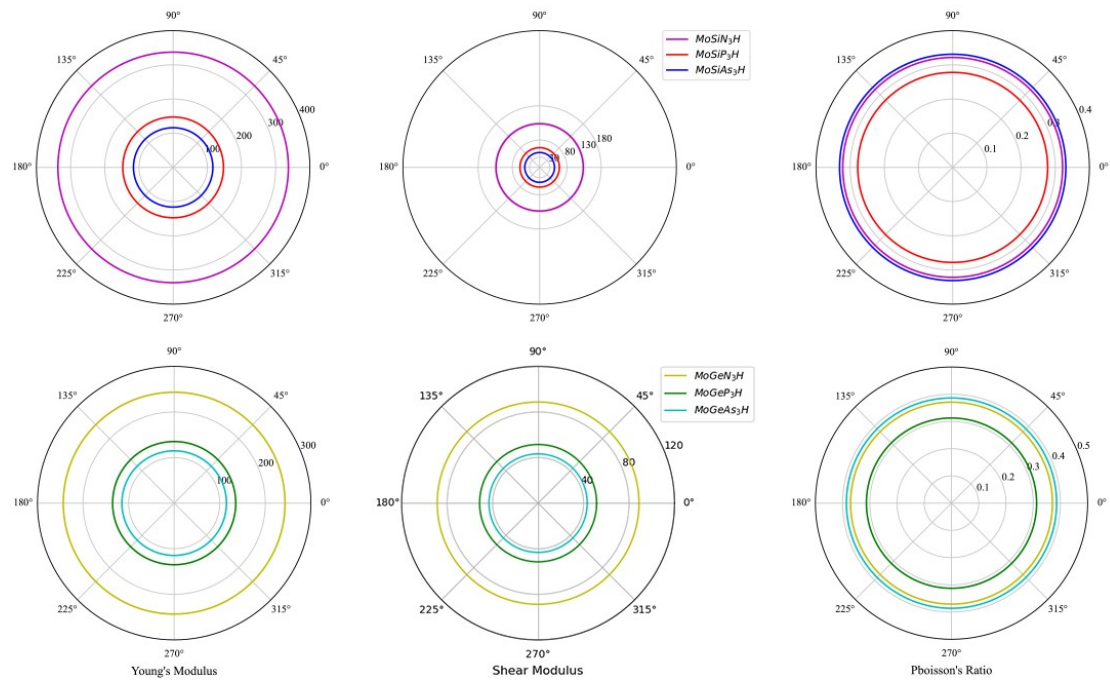


Fig. S2 Polar diagrams of Young's modulus, shear modulus and Poisson ratio of MoAZ₃H ML.

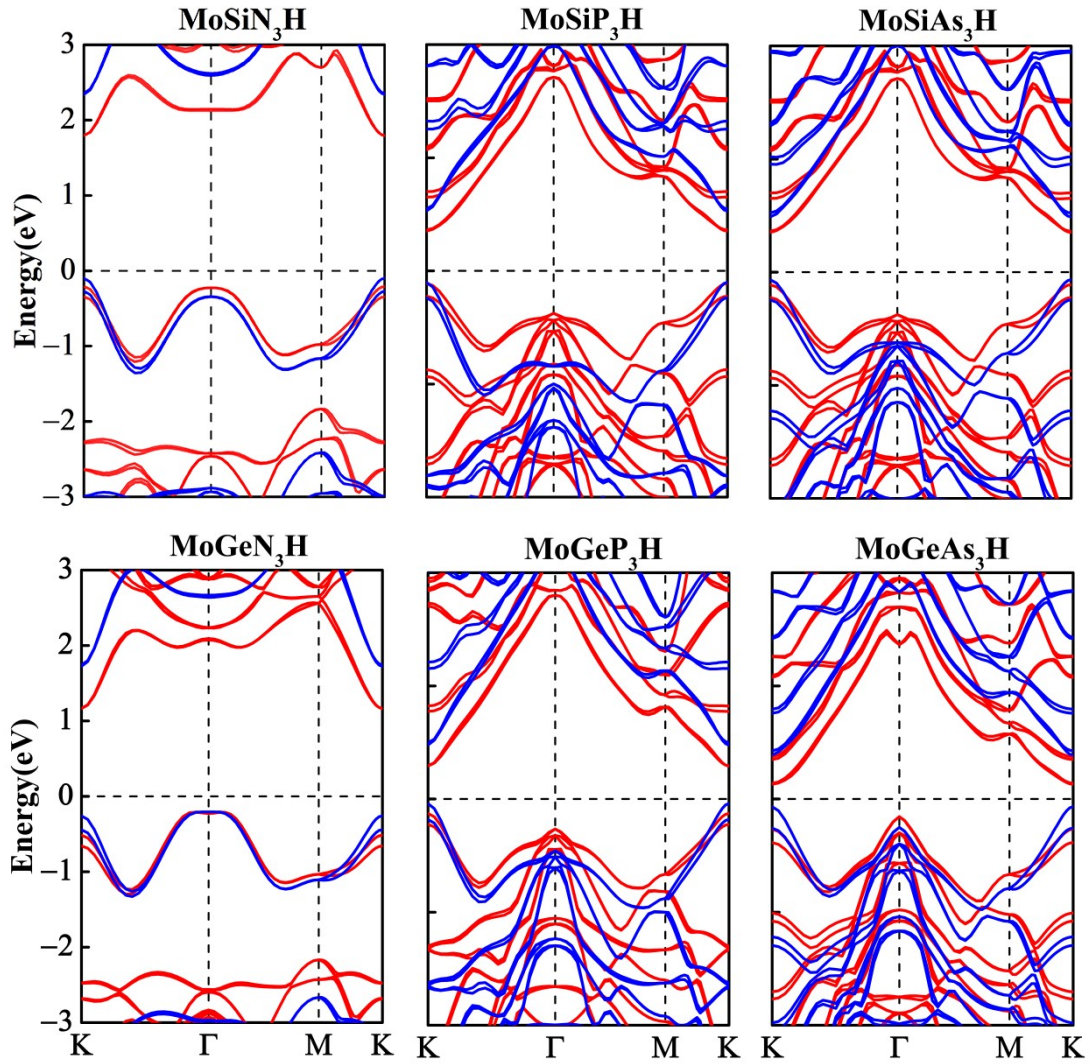


Fig. S3 Band structure diagram of MoAZ₃H ML calculated by PBE+SOC (red lines) and HSE+SOC (blue lines) functionals, with Fermi energy level set to 0.

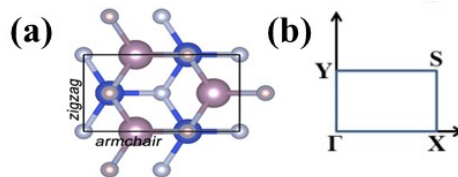


Fig. S4 (a) Top view of the rectangular unit cell and (b) the corresponding high symmetry path in the Brillouin zone for the MoAZ₃H ML.

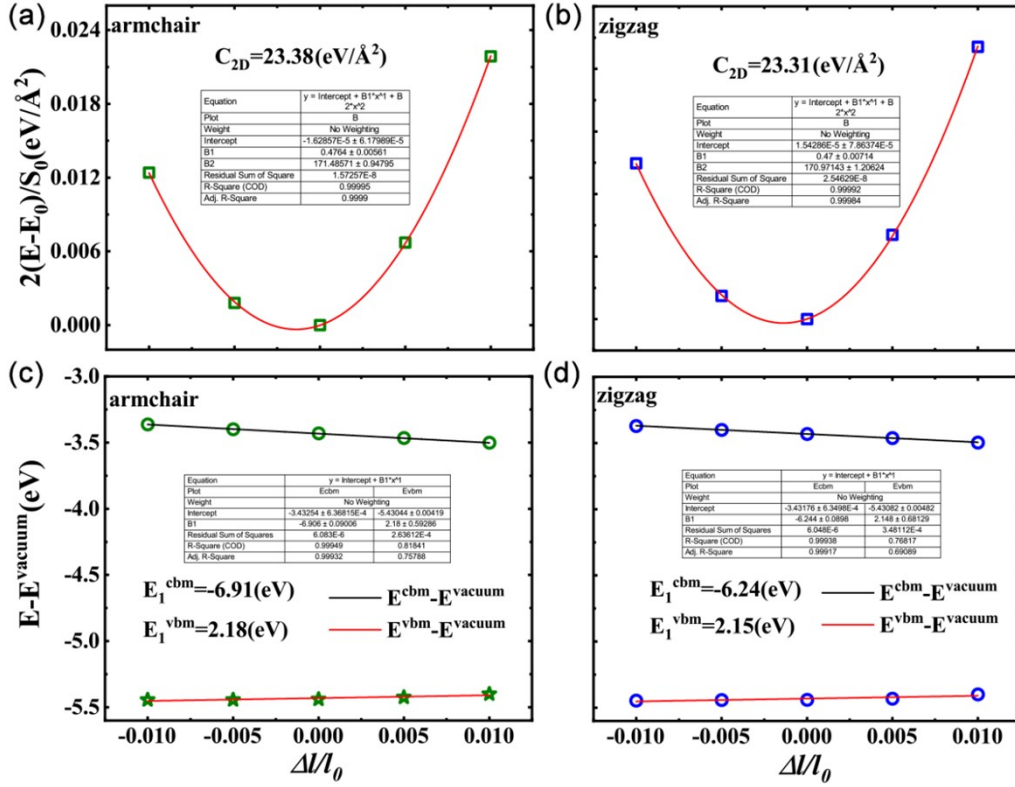


Fig. S5 In-plane stiffness and deformation potential of the MoSiN₃H ML obtained from the PBE+SOC scheme.

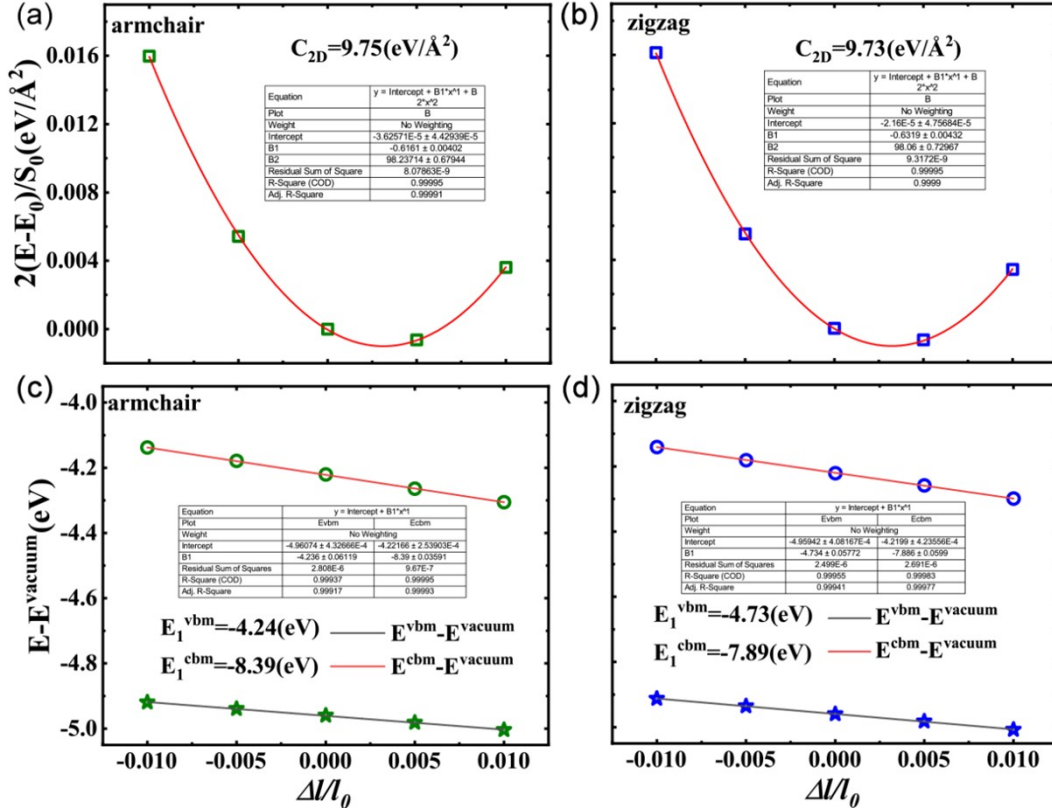


Fig. S6 In-plane stiffness and deformation potential of the MoSiP₃H ML obtained from the PBE+SOC scheme.

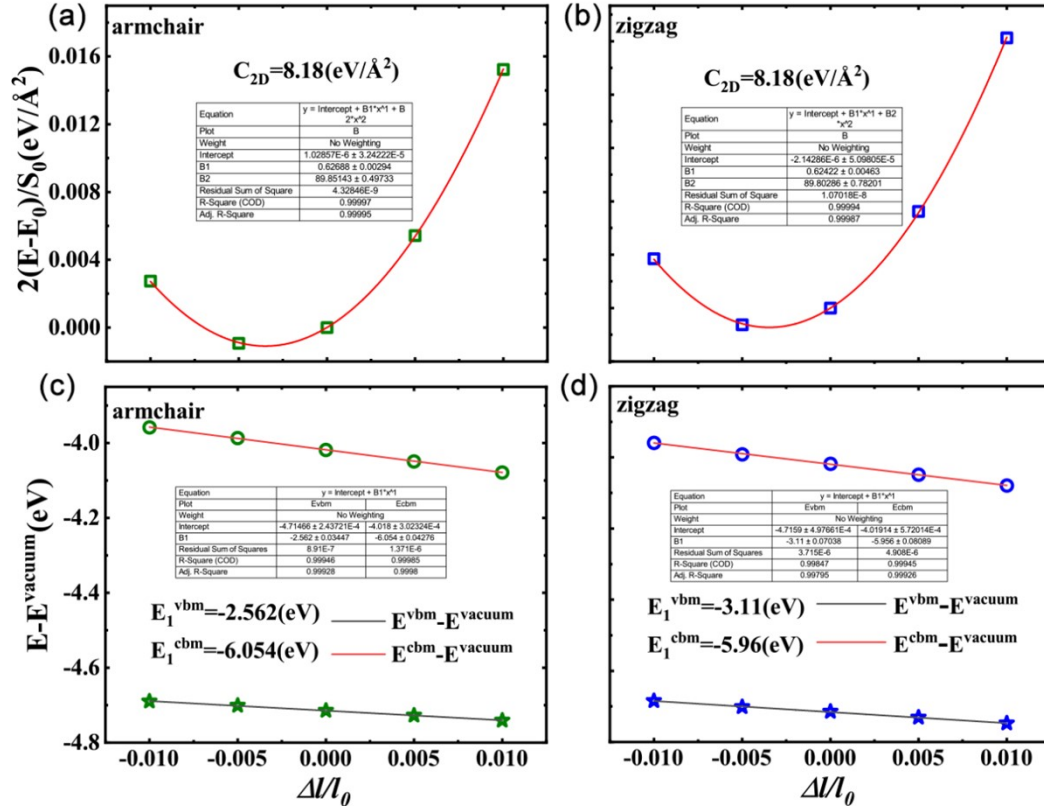


Fig. S7 In-plane stiffness and deformation potential of the MoSiAs₃H ML obtained from the PBE+SOC scheme.

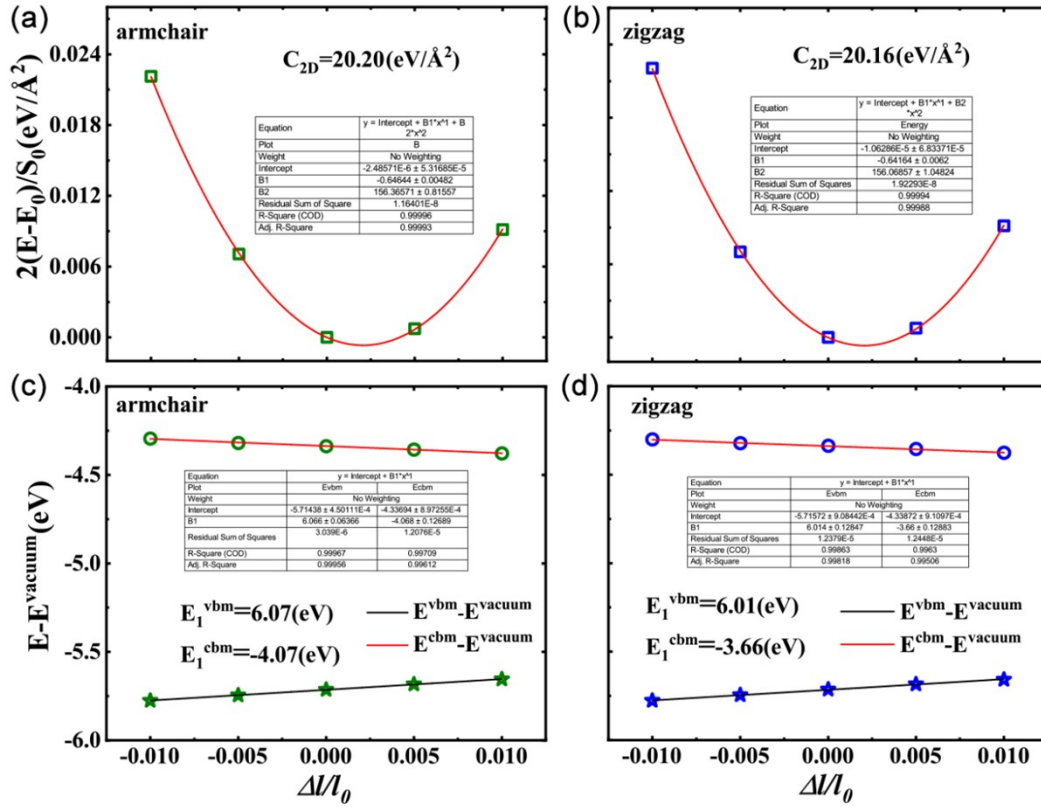


Fig. S8 In-plane stiffness and deformation potential of the MoGeN₃H ML obtained from the PBE+SOC scheme.

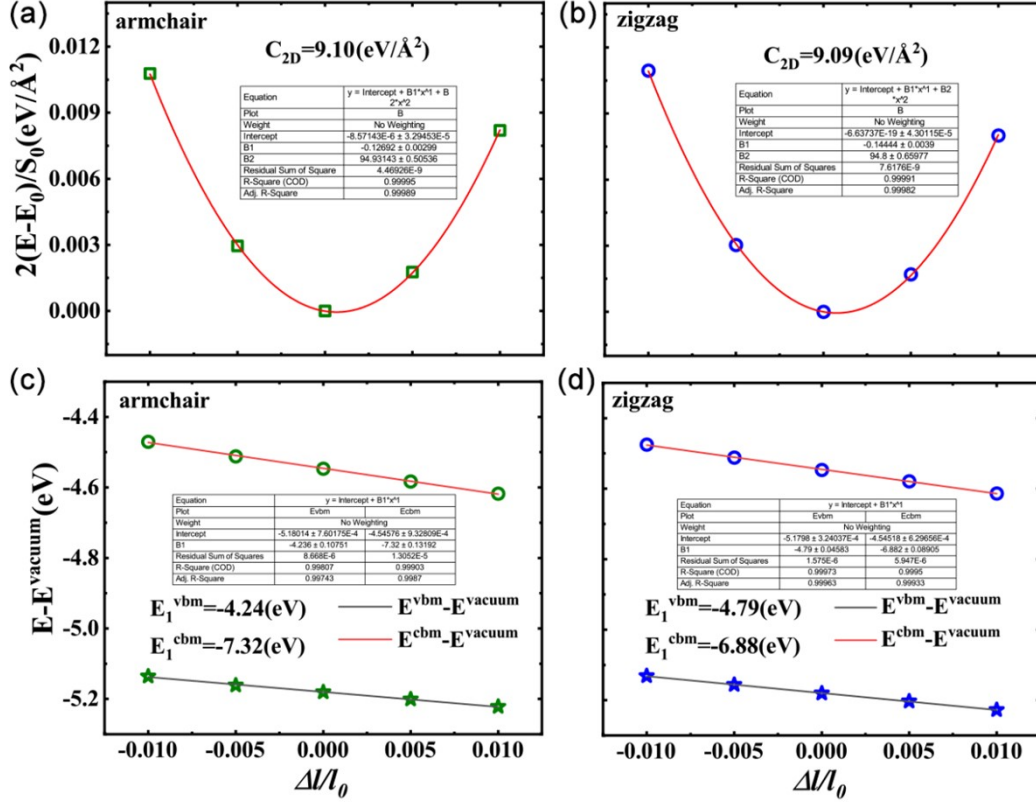


Fig. S9 In-plane stiffness and deformation potential of the MoGeP₃H ML obtained from the PBE+SOC scheme.

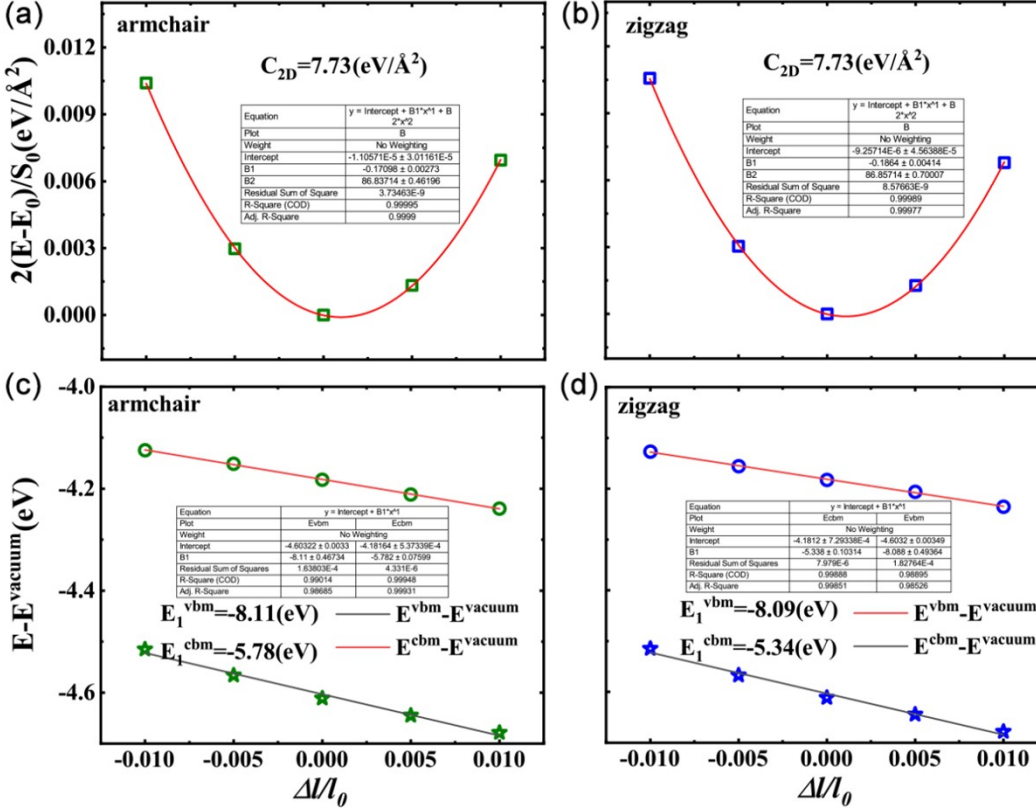


Fig. S10 In-plane stiffness and deformation potential of the MoGeAs₃H ML obtained from the PBE+SOC scheme.